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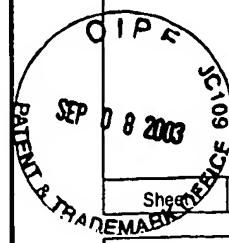
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Sheet

1

of

		Complete If Known	
		Application Number	10/620,516
		Filing Date	July 16, 2003
		First Named Inventor	Udayakumar et al.
		Group Art Unit	
		Examiner Name	
		Attorney Docket No.	TI-35996



U.S. PATENT DOCUMENTS					
Exam. Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)
		Number	Kind Code ² (if known)		
SWL	AA	6,144,060		Park et al.	11/07/2000
SWL	AB	6,225,656	B1	Cuchiaro et al.	05/01/2001
	AC				
	AD				
	AF				
	AG				
	AH				

FOREIGN PATENT DOCUMENTS					
Exam. Initials*	Cite No. ¹	Foreign Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)
		Office ³	Number ⁴		
	BA				
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS					
Exam. Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			
SWL	CA	Notes taken at the International Symposium on Applications of Ferroelectrics Conference in Nara, Japan in May, 2002. The speaker was H. Nagel of Infineon Technologies and Toshiba Corporation, Key Technologies for High Density FeRAM Application, one page.			
	CB				
	CC				
	CD				
	CE				
	CF				
	CG				
	CH				

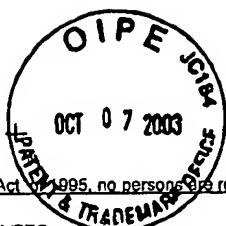
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US and Foreign Patent Documents: ¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

Other Prior Art/Non-Patent Literature Documents: ¹Unique citation designation number. ²Applicant is to place a check mark here if English Translation is attached.

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		Group Art Unit	
		Examiner Name	
Sheet	2	of	2
		Attorney Docket No.	
		TI-35996	

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Exam. Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
SWC	CG	"Comparison Between HCP CVD and PECVD Silicon Nitride for Advanced Interconnect Applications", J. YOTA, M. JANANI, L.E. CAMILLETTI, A. KAR-ROY, Q.Z. LIU, C. NGUYEN, M.D. WOO, J. HANDER, and P. VAN CLEEMPUT, IEEE, 2000, pgs. 76-78.	
SWC	CH	"Hydrogen Role on the Properties of Amorphous Silicon Nitride", F. DE BRITO MOTS, J.F. JUSTO and A. FAZZIO, Journal of Applied Physics, Volume 86, Number 4, August 15, 1999, pgs. 1843-1847.	
	CI		
	CJ		
	CK		
	CL		
	CM		
	CN		
	CO		
	CP		

Examiner Signature	CRANE	Date Considered	3/18/04
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Sheet	1	of	2	Attorney Docket No.	TI-35996
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U.S. PATENT DOCUMENTS

Exam. Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm- dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
SWC	AA	5,452,178		Emesh et al.	09/19/1995	Entire Document
	AB	5,972,722		Visokay et al.	10/26/1999	Entire Document
	AC	6,090,697		Xing et al.	07/18/2000	Entire Document
	AD	6,177,351	B1	Beratan et al.	01/23/2001	Entire Document
	AE	6,242,299	B1	Hickert	06/05/2001	Entire Document
	AF	6,261,967	B1	Athavale et al.	07/17/2001	Entire Document
	AG	6,291,251	B1	Nam	09/18/2001	Entire Document
	AH	6,423,592	B1	Sun	07/23/2002	Entire Document
	AI	6,495,413	B2	Sun et al.	12/17/2002	Entire Document
	AJ	6,528,386	B1	Summerfelt et al.	03/04/2003	Entire Document
	AK	6,534,809	B2	Moise et al.	03/18/2003	Entire Document
	AL	6,576,482	B1	Aggarwal et al.	06/10/2003	Entire Document
	AM	6,611,014	B1	Kanaya et al.	08/26/2003	Entire Document
SWC	AN	2001/0034106	A1	Moise et al.	10/25/2001	Entire Document
SWC	AO	2001/0044205	A1	Gilbert et al.	11/22/2001	Entire Document

FOREIGN PATENT DOCUMENTS

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SWC	CA	"FeRAM Tutorial", ALI SHEIKHOLESLAMI and P. GLENN GULAK, A survey of circuit Innovations In Ferroelectric random-access memories, Proceedings of the IEEE, Vol. 88, No. 3, May, 2000, 3 pages, taken from the Internet at: http://www.eecg.toronto.edu/~ali/ferro/tutorial.html .	
	CB	"A survey of Circuit Innovations In Ferroelectric Random Access Memories", ALI SHEIKHOLESLAMI and P. GLENN GULAK, Proceedings of the IEEE, Vol. 88, No. 5, May, 2000, pp. 667-689.	
	CC	"Generic CVD Reactor", CVD Basics, DANIEL M. DOBKIN, Dec. 7, 2001, 3 pages, taken from the Internet at: http://www.batn.t.com/~nigmatics/semiconductor_processing/CVD_Fundamentals/introdu...	
	CD	"Physical Vapor Deposition", Cougar Labs, Inc., Dec. 7, 2001, 9 pages, taken from the Internet at: http://www.cougarlabs.com/pvd1.html .	
	CE	"The Hydrogen Content of Plasma-Deposited silicon Nitrid", W. A. LANFORD and M. J. RAND, American Institute of Physics, J. Appl. Phys. 49(4), April, 1978, Pgs. 2473-2477.	
SWC	CF	"Free Energy Model for the Analysis of Bonding in a-Si _x N _y H _z Alloys", Z. YIN and W. SMITH, J. Vac. Sci. Technol. A, Volume 9, No. 3, May/June, 1991, pg. 972.	

CRANE

3/18/04